

MM120G3T65BM

650V 120A IGBT

RoHS Compliant

June 2020

Version 01

PRODUCT FEATURES

APPLICATIONS

Unit

W

V

g

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$I_F(A)$

$V_F(V)$

Figure 7. Diode Forward Characteristics Diode

$E_{REC}(mJ)$

R_g

Figure 8. Switching Energy vs Gate Resistor Diode

$E_{REC}(mJ)$

$Z_{thjc}(K/W)$

I_{FAD}

Rectangular Pulse Duration, t_{SD}

